

DHG60U1200LB

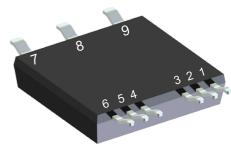
Sonic Fast Recovery Diode

V_{RRM}	=	1200 V		
I _{dav}	=	60 A		
t _{rr}	=	160 ns		

High Performance Fast Recovery Diode Low Loss and Soft Recovery 3~ Rectifier Bridge

Part number

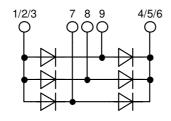
DHG60U1200LB



Backside: isolated



20190404d



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviourAvalanche voltage rated for reliable
- operationSoft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
 - Soldering pins for PCB mounting
 - Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littlefuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littlefuse.com/disclaimer-electronics.

IXYS reserves the right to change limits, conditions and dimensions.



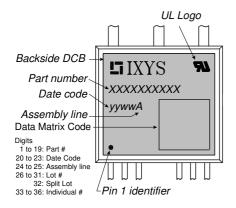
DHG60U1200LB

Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockin	$T_{VJ} = 25^{\circ}C$			1200	V	
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{vJ} = 25^{\circ}C$			1200	V
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			50	μA
		V _R = 1200 V	$T_{vJ} = 125^{\circ}C$			0.5	mA
V _F	forward voltage drop	I _F = 20 A	$T_{VJ} = 25^{\circ}C$			2.00	V
		I _F = 60 A				2.92	V
		I _F = 20 A	T _{vJ} = 125°C			1.94	V
		$I_{F} = 60 \text{ A}$				3.15	V
I DAV	bridge output current	$T_c = 80^{\circ}C$	T _{vJ} = 150°C			60	А
		rectangular $d = \frac{1}{3}$					
V _{F0}	threshold voltage	$T_{vJ} = 150^{\circ}C$			1.35	V	
r _F	slope resistance } for power los				29	mΩ	
R _{thJC}	thermal resistance junction to case					1.2	K/W
R _{thCH}	thermal resistance case to heatsink				0.40		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			100	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α
C	junction capacitance	$V_{R} = 600 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		11		pF
I _{RM}	max. reverse recovery current		$T_{vJ} = 25 °C$		19		Α
		$I_F = 20 \text{ A}; V_R = 600 \text{ V}$	T _{vJ} = 125 °C		25		Α
t _{rr}	reverse recovery time	I _F = 20 A; V _R = 600 V -di _F /dt = 600 A/μs	$T_{VJ} = 25 °C$		160		ns
)		T _{vJ} = 125 °C		280		ns

20190404d



Package SMPD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
	RMS current	per terminal				100	Α
T _{vj}	virtual junction temperature			-55		150	°C
T_{op}	operation temperature			-55		125	°C
T _{stg}	storage temperature			-55		150	°C
Weight					8.5		g
F _c	mounting force with clip			40		130	Ν
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	1.6			mm
d _{Spb/Apb}			terminal to backside	4.0			mm
V	isolation voltage t = 1 second t = 1 minute	t = 1 second		3000			۷
		50/60 Hz, RMS; liso∟ ≤ 1 mA	2500			v	



Part description



- H = Sonic Fast Recovery Diode
- G = extreme fast
- 60 = Current Rating [A]
- U = 3~ Rectifier Bridge
- 1200 = Reverse Voltage [V]
- LB = SMPD-B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG60U1200LB-TUB	DHG60U1200LB-TUB	Tube	20	524936
Alternative	DHG60U1200LB-TRR	DHG60U1200LB	Tape & Reel	200	524950

Equivalent Circuits for Simulation		* on die level	$T_{vJ} = 150 \ ^{\circ}C$	
	- Ro-	Fast Diode		
V _{0 max}	threshold voltage	1.35		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	27		mΩ

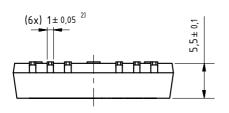
IXYS reserves the right to change limits, conditions and dimensions.

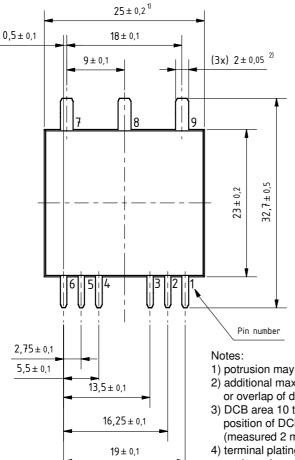
20190404d



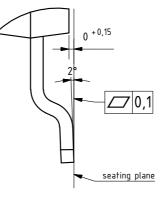
DHG60U1200LB

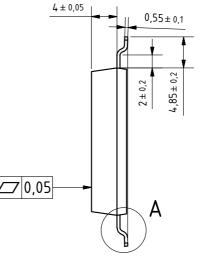
Outlines SMPD





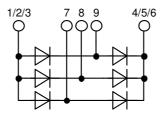
A (8:1)





1) potrusion may add 0.2 mm max. on each side

- 2) additional max. 0.05 mm per side by punching misalignement or overlap of dam bar or bending compression
- DCB area 10 to 50 μm convex; position of DCB area in relation to plastic rim: ±25 μm (measured 2 mm from Cu rim)
- 4) terminal plating: 0.2 1 μm Ni + 10 25 μm Sn (gal v.) cutting edges may be partially free of plating

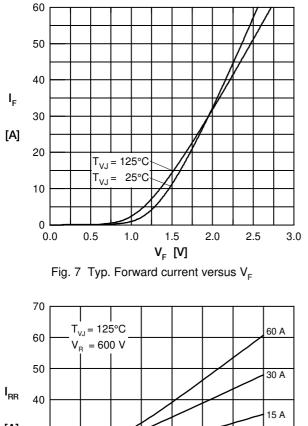


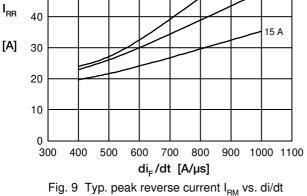
IXYS reserves the right to change limits, conditions and dimensions.

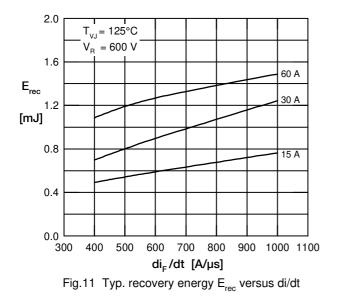
20190404d

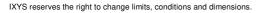


Fast Diode

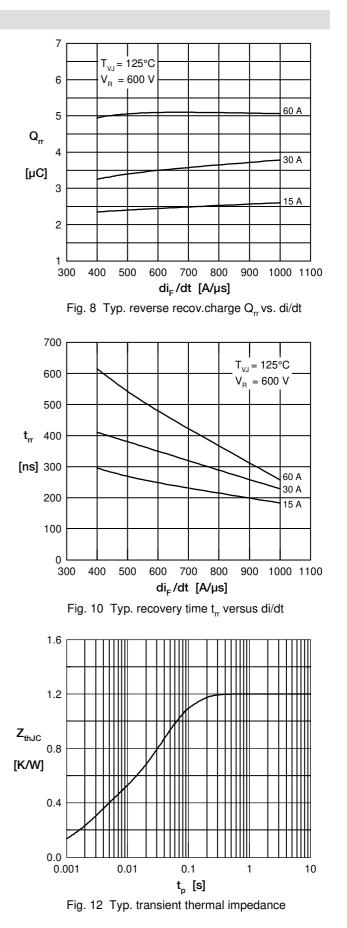












X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bridge Rectifiers category:

Click to view products by IXYS manufacturer:

Other Similar products are found below :

 MB2510
 MB252
 MB356G
 MB358G
 GBJ1504-BP
 GBU15J-BP
 GBU15K-BP
 GBU4A-BP
 GBU6B-E3/45
 GSIB680-E3/45
 DB101-BP

 DF01
 DF10SA-E345
 BU1508-E3/45
 KBPC50-10S
 RS405GL-BP
 G5SBA60-E3/51
 GBU10J-BP
 GBU6M
 GBU8D-BP
 GBU8J-BP

 2KBB10
 36MB140A
 TB102M
 MB1510
 MB258
 MB6M-G
 MB86
 TL401G
 MDA920A2
 TU602
 TU810
 MP501W-BP
 MP502-BP

 BR101-BP
 BR84DTP204
 BU2008-E3/51
 KBPC10/15/2501WP
 KBPC25-02
 VS-2KBB60
 DF06SA-E345
 DF1510S
 VS-40MT160PAPBF

 W02M
 GBL02-E3/45
 GBU4G-BP
 GBU6B-E3/51
 GSIB15A80-E3/45
 DB104-BP